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ALEXIA VRAHIMIS

Date: December 26, 2001

U.S. Patent and Trademark Office

P.O. Box 2327

Arlington, VA 22202

Sir:

Enclosed herewith are the necessary papers for filing the following application for Letters Patent:

Applicant : WALTER HARTNER ET AL.

Title : METHOD FOR FABRICATING A PRECIOUS-METAL ELECTRODE

5 sheets of formal drawings.

The payment in the amount of \$ 992.00 covering the filing fee.

PCT Cover Sheet WO 01/01462 A1.

This application is being filed without a signed oath or declaration under the provisions of 37 CFR 1.53(f). Applicants await notification of the date by which the oath or declaration and the surcharge are due, pursuant to this rule.

The Patent and Trademark Office is hereby given authority to charge Deposit Account No. 12-1099 of Lerner and Greenberg, P.A. for any fees due or deficiencies of payments made for any purpose during the pendency of the above-identified application.

Respectfully submitted,

  
For Applicants

LAG:kf



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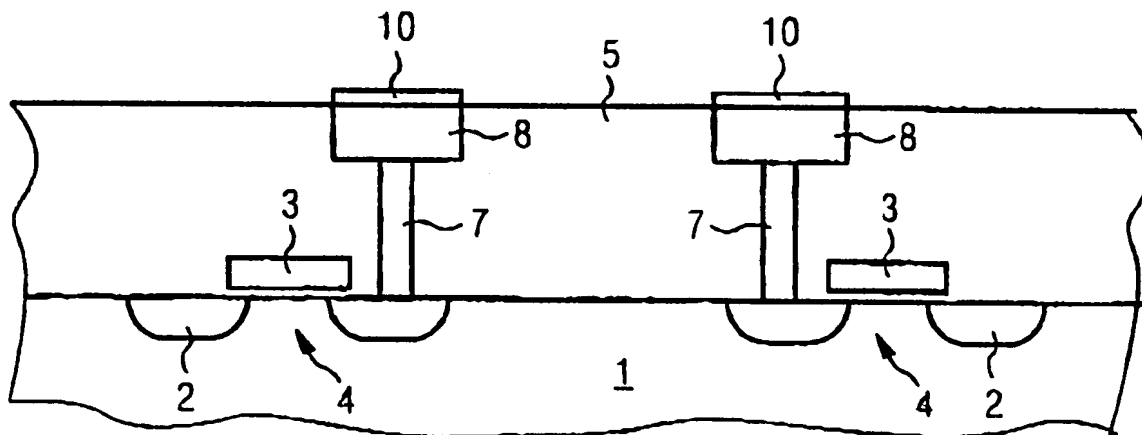
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*[Fortsetzung auf der nächsten Seite]*

(54) Title: **METHOD FOR PRODUCING A NOBLE-METAL ELECTRODE**

(54) Bezeichnung: **VERFAHREN ZUR HERSTELLUNG EINER EDELMETALLELEKTRODE**



(57) Abstract: The invention relates to a method for producing a structured noble-metal layer, in particular, for producing a structured noble-metal layer in an integrated circuit, which consists of the following stages: a) a substrate is prepared, comprising at least one catalytically active connection zone and at least one catalytically inactive insulation zone; and b) at least one organometallic compound of a noble metal is fed to the substrate at a temperature of between 0 ° and 120 °C in such a way that the noble metal is deposited selectively onto the catalytically active connection zone. The inventive method has the advantage that the layer material, which can often only be etched with difficulty, does not need to be directly structured. The desired structure of the layer is predetermined by the pre-structuring of the substrate in a connection zone and in an insulation zone and is created by the selective deposition process.

(57) Zusammenfassung: Erfindungsgemäß wird ein Verfahren zur Herstellung einer strukturierten Edelmetallschicht, insbesondere zur Herstellung einer strukturierten Edelmetallschicht in einer integrierten Schaltung, bereitgestellt, das folgende Schritte aufweist: a) ein Substrat mit zumindest einem katalytisch aktiven Anschlußbereich (8) und zumindest einem katalytisch inaktiven Isolationsbereich (5, 14) wird bereitgestellt; und b) zumindest eine metallorganische Verbindung eines Edelmetalls wird bei einer Temperatur von 0 ° bis 120 °C zu dem Substrat geführt, so daß

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